

|    | Hits | Search Text  | DBs  |
|----|------|--|--|
| 23 | 3    | ((substrate or wafer) same<br>((tetracarboxylic near2<br>dianhydride) or<br>\$4dioxatricyclo\$6dodecane\$6tetraon<br>e) same ((alicyclic near3 diamine)<br>or diaminocyclohexane or<br>isophoronediamine or<br>bisaminomethylcyclohexane)) and<br>(expos\$3 or imaging or irradiat\$4<br>or illuminat\$4 or pattern\$4) and<br>((dielectric or TiO or TiN or SiN)<br>same (substrate or wafer)) and<br>((metal\$4 or conductive or wir\$3)<br>same (pattern or cavity or line))<br>and ((develop\$4 or strip\$4 or<br>remov\$3) same (polymer or<br>photoresist or resist or polyimide<br>or polyamide)) | US-PGPUB;<br>USPAT; USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |
| 24 | 5    | (((tetracarboxylic near2<br>dianhydride) or<br>\$4dioxatricyclo\$6dodecane\$6tetraon<br>e) same ((alicyclic near3 diamine)<br>or diaminocyclohexane or<br>isophoronediamine or<br>bisaminomethylcyclohexane)) and<br>(expos\$3 or imaging or irradiat\$4<br>or illuminat\$4 or pattern\$4) and<br>((dielectric or TiO or TiN or SiN)<br>same (substrate or wafer)) and<br>((metal\$4 or conductive or wir\$3)<br>same (pattern or cavity or line))<br>and ((develop\$4 or strip\$4 or<br>remov\$3) same (polymer or<br>photoresist or resist or polyimide<br>or polyamide))                              | US-PGPUB;<br>USPAT; USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |

|    | Hits | Search Text   | DBs  |
|----|------|---|--|
| 25 | 3    | 430/322.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3) | US-PGPUB;<br>USPAT; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 26 | 3    | 430/324.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3) | US-PGPUB;<br>USPAT; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 27 | 3    | 430/325.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3) | US-PGPUB;<br>USPAT; EPO;<br>JPO; DERWENT;<br>IBM_TDB |

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| 28 | 3        | 430/270.1.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3) | US-PGPUB;<br>USPAT; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 29 | 4        | "430"/\$.ccls. and ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)  | USOCR  |
| 30 | 4        | ((substrate or wafer) same (polyimide or polyamic) same (expos\$ or imaging or irradiat\$4 or illuminat\$4) same develop\$4 same pattern\$4) and ((dielectric or TiO or TiN or SiN) same first) and ((dielectric or TiN or SiN or TiO) same second) and ((remov\$3 or strip\$4) same (polymer\$3 or photoresist or resist) same pattern) and (metal\$3 or conductive or wir\$3)                     | USOCR  |

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|----|----------|--|----------|
| 31 | 1        | (((tetracarboxylic near2 dianhydride) or \$4dioxatricyclo\$6dodecane\$6tetraone) same ((alicyclic near3 diamine) or diaminocyclohexane or isophoronediamine or bisaminomethylcyclohexane)) and (expos\$3 or imaging or irradiat\$4 or illuminat\$4 or pattern\$4) and ((dielectric or TiO or TiN or SiN) same (substrate or wafer)) and ((metal\$4 or conductive or wir\$3) same (pattern or cavity or line)) and ((develop\$4 or strip\$4 or remov\$3) same (polymer or photoresist or resist or polyimide or polyamide))).clm. | US-PGPUB |
| 32 | 1        | (((tetracarboxylic near2 dianhydride) or \$4dioxatricyclo\$6dodecane\$6tetraone) same ((alicyclic near3 diamine) or diaminocyclohexane or isophoronediamine or bisaminomethylcyclohexane)) and (expos\$3 or imaging or irradiat\$4 or illuminat\$4 or pattern\$4) and ((dielectric or TiO or TiN or SiN) same (substrate or wafer)) and ((metal\$4 or conductive or wir\$3) same (pattern or cavity or line)) and ((develop\$4 or strip\$4 or remov\$3) same (polymer or photoresist or resist or polyimide or polyamide)))      | US-PGPUB |